

IN THE CLAIMS:

Listing of claims:

1. (previously presented) A method for forming a head suspension assembly, comprising:
 - forming a trench extending into a substrate;
 - forming a sacrificial layer in the trench;
 - forming a film across the substrate;
 - patterning a photoresist layer on top of the film;
 - transferring an image of the patterned photoresist layer through the film;
 - removing the patterned photoresist layer; and
 - removing the sacrificial layer from the trench to form a cavity extending a distance into the substrate.
2. (previously presented) A method as in claim 1, wherein the film includes silicon.
3. (previously presented) A method as in claim 1, wherein the transferring the image of the patterned photoresist layer through the film is done using reactive ion etching.
4. (original) A method as in claim 1, wherein the substrate comprises silicon and the sacrificial layer is formed by etching a trench in the substrate and filling the trench with a metal.
5. (original) A method as in claim 4, wherein removing the sacrificial layer comprises etching the metal from the trench.
6. (previously presented) A method as in claim 1, further comprising forming the film from a polymer material.

7. (previously presented) A method as in claim 1, wherein the substrate comprises silicon and the film comprises polysilsesquioxone.

8. (previously presented) A method as in claim 1, wherein the cavity extends a width that is no greater than that of the substrate and the cavity extends a depth that is less than a depth of the substrate.

9. (previously presented) A method as in claim 1, further comprising forming an adhesion layer between the substrate and the film.

10. (previously presented) A method as in claim 3, wherein the film comprises a resin, and positioning a slider on the resin after the removing the sacrificial layer.

11. (canceled)

12. (currently amended) A method as in claim ~~13~~ 11, further comprising, prior to forming the photoresist layer, curing the polysilsesquioxone layer.

13. (currently amended) A method as in claim 11, ~~further comprising,~~ for forming a head suspension assembly, comprising:

forming a polysilsesquioxone layer over a portion of a substrate;

forming a photoresist layer on the polysilsesquioxone layer;

patterning the photoresist layer;

etching the polysilsesquioxone layer using the patterned photoresist layer as a mask;

removing the patterned photoresist layer; and

prior to forming the polysilsesquioxone layer, forming a trench in the substrate and forming a sacrificial layer in the trench, wherein the polysilsesquioxone layer is formed over the sacrificial layer.

14. (original) A method as in claim 13, further comprising forming the sacrificial layer from a metal material.

15. (original) A method as in claim 13, further comprising forming the sacrificial layer from copper.

16. (original) A method as in claim 13, further comprising removing the sacrificial material from the trench after the etching the polysilsesquioxone layer.

17. (currently amended) A method as in claim 13, ~~12~~, further comprising positioning a slider on the cured polysilsesquioxone layer after the removing the patterned photoresist layer.

18-20. (canceled)